Application No.:

10/686,893

Amendment Dated: Reply to Office Action of: February 27, 2007 October 27, 2006 YAO-3990US3

MAR 0 1 2007 A

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Appln. No:

10/686,893

Applicants:

Hidetoshi ISHIDA, et al.

Filed:

October 16, 2003

Title:

ETCHANT AND METHOD FOR FABRICATING A SEMICONDUCTOR

**DEVICE USING THE SAME** 

TC/A.U.:

2823

Examiner:

Q. Jefferson

Commination

Confirmation No.: 8582

Docket No.:

YAO-3990US3

## AMENDMENT UNDER 37 C.F.R. § 1.116

## **Expedited Procedure**

## Mail Stop AF

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

 $\boxtimes$ 

amend the above-identified application as follows:

Amendments to the Specification begin on page of this paper.

Amendments to the Claims are reflected in the listing of claims which begins on page 2 of this paper.

Amendments to the Drawings begin on page of this paper and include an attached replacement sheet(s).

Amendments to the Abstract are on page of this paper. A clean version of the Abstract is on page of this paper.

Remarks/Arguments begin on page 3 of this paper.

Responsive to the Final Office Action dated October 27, 2006, please